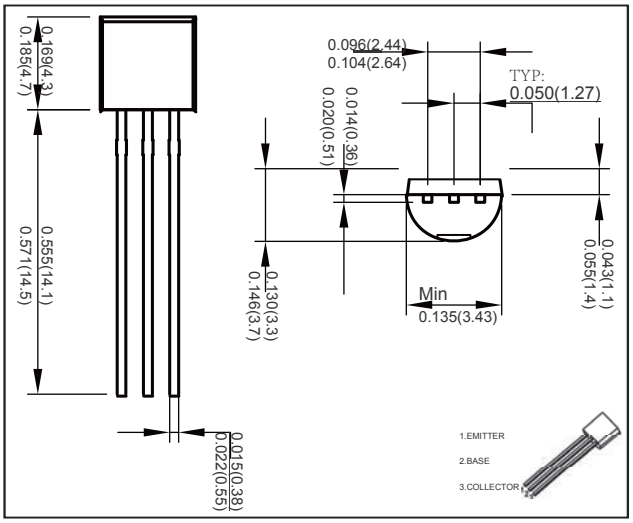
TO-92 Plastic-Encapsulate Transistors

FEATURES

- Switching and amplification in high voltage
- Applications such as telephony
- Low current(max. 600mA)
- High voltage(max.150V)
- PNP General Purpose Amplifier

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

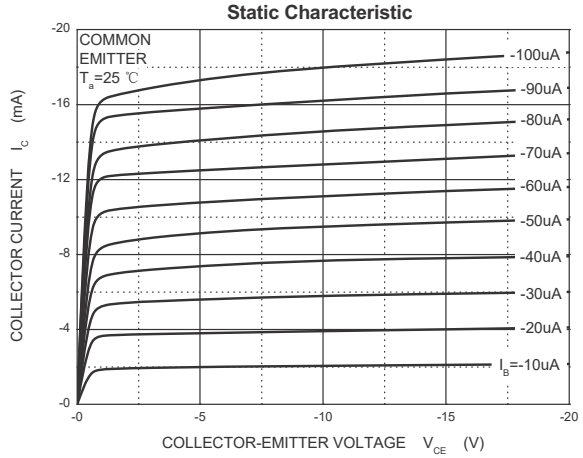
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-160	V
Collector-Emitter Voltage	V_{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-0.6	A
Collector Power Dissipation	P_C	625	mW
Thermal Resistance From Junction To Ambient	R_{KJA}	200	℃ /W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55~+150	℃

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -0.1mA,I_E=0	-160			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= -1mA,I_B=0	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -0.01mA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	VCB= - 120 V, IE = 0			-50	nA
Emitter cut-off current	I_{EBO}	V_{EB}= -3V,I_C=0			-50	nA
DC current gain	$h_{FE(1)}$	V_{CE}= -5 V, I_C= -1 mA	80			
	$h_{FE(2)}$	V_{CE}= -5 V, I_C= -1 0 mA	100		300	
	$h_{FE(3)}$	V_{CE}= -5 V, I_C= -5 0mA	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= -50mA,I_B= -5mA			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C= -50mA,I_B= -5mA			-1	V
Transition frequency	f_T	VCE= -5V,IC= -10mA, f =30MHz	100		300	

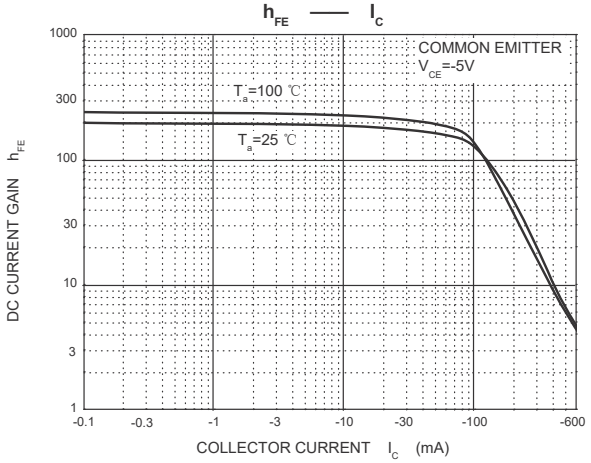
* Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%.

RATINGS AND CHARACTERISTIC CURVES

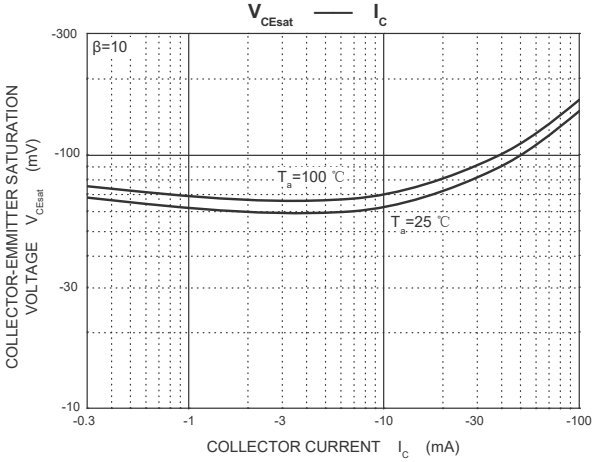
Static Characteristic



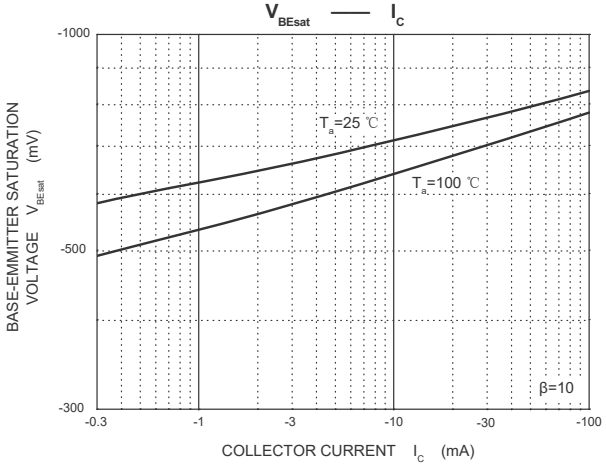
hFE —— IC



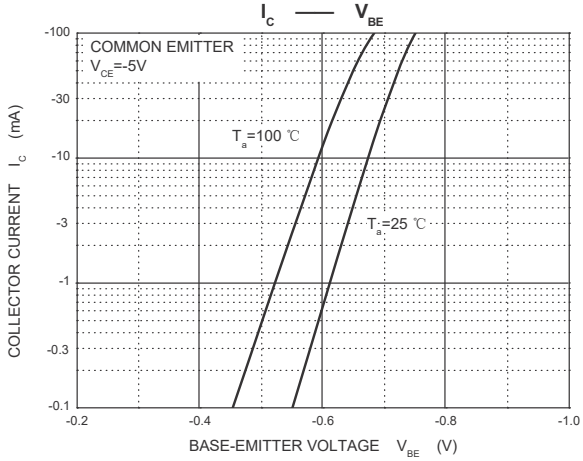
VCEsat —— IC



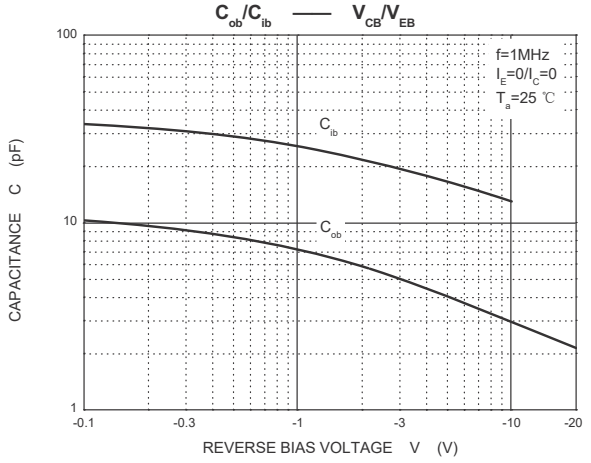
VBEsat —— IC



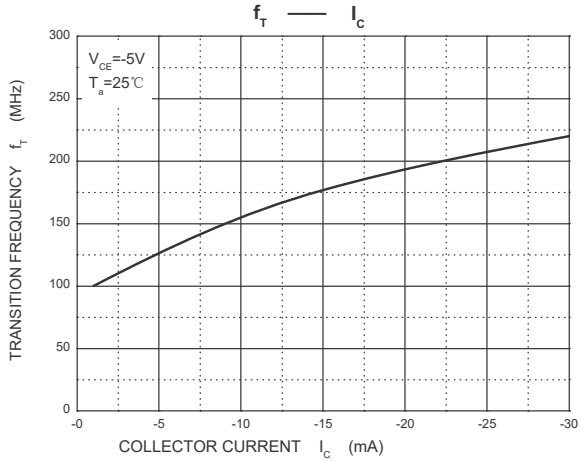
IC —— VBE



Cob/Cib —— VCB/VEB



fT —— IC



PC —— Ta